XTREME EUV light source program gets cash boost from Intel

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Intel Corporation has via its venture capital arm invested an undisclosed sum in XTREME technologies GmbH a joint venture between JENOPTIK AG and USHIO Inc to boost the development cycle of its 13.5nm light source."This investment enables us to expand our development efforts and to strengthen our leadership position in the emerging EUV market," said Dr. Uwe Stamm, President of XTREME technologies GmbH.

The XTREME team had revealed last year that the use of a gas discharged produced plasma (GDPP) with tin as a source fuel was two to three times more efficient than xenon at converting electromagnetic or laser energy to EUV light.

However, considerable development was still required due to the debris/contamination issues of using tin for the collector and heat damage to the mirrors, which seriously impact lifetime operation.

Intel has long been a technology champion of EUV Lithography and has plans to adopt the technology if ready at the 32nm node.

"Intel Capital is excited to lead investments in innovative companies in the semiconductor manufacturing equipment infrastructure space around the world", said Keith Larson, Intel Capital Managing Director. "Intel Capital funding for XTREME technologies is aimed at accelerating development and commercialization of EUV light sources for production-worthy EUV photolithography equipment."

Much of the work so far carried out by XTREME has been part of the MEDEA+ "T405" project as part of a European effort to develop a complete sub-system set of required components for a European designed and built EUV Lithography system with ASML. The T405 project has now ended.